# High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications

# **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	IC	1.0	Vdc
Collector Current – Peak	ICM	2.0	Α

### THERMAL CHARACTERISTICS

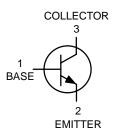
Characteristic	Symbol	Max	Unit
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 1.)	310 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θ</sub> J <sub>A</sub> (Note 1.)	403	°C/W
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub> (Note 2.)	710 5.7	mW mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub> (Note 2.)	176	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P <sub>Dsingle</sub>	575	mW
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

- 1. FR-4 @ Minimum Pad
- 2. FR-4 @ 1.0 X 1.0 inch Pad



http://onsemi.com

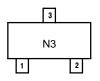
# 30 VOLTS 2.0 AMPS NPN TRANSISTOR





SOT-23 (TO-236) CASE 318-08 STYLE 6

### **DEVICE MARKING**



N3 = Specific Device Code

### **ORDERING INFORMATION**

Device	Package	Shipping
MMBT489LT1	SOT-23	3000/Tape & Reel

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	30	-	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 0.1 mAdc, I <sub>E</sub> = 0)	V(BR)CBO	50	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 0.1 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	5.0	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	ICBO	_	0.1	μAdc
Collector–Emitter Cutoff Current (VCES = 30 Vdc)	ICES	_	0.1	μAdc
Emitter Cutoff Current (VEB = 4.0 Vdc)	I <sub>EBO</sub>	-	0.1	μAdc
ON CHARACTERISTICS			1	•
DC Current Gain (Note 1.) (IC = 50 mA, VCE = 5.0 V) (IC = 0.5 A, VCE = 5.0 V) (IC = 1.0 A, VCE = 5.0 V)	hFE	300 300 200	900 -	
Collector–Emitter Saturation Voltage (Note 1.) (I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 100 mA) (I <sub>C</sub> = 0.5 A, I <sub>B</sub> = 50 mA) (I <sub>C</sub> = 0.1 A, I <sub>B</sub> = 1.0 mA)	VCE(sat)	- - -	0.200 0.125 0.075	V
Base–Emitter Saturation Voltage (Note 1.) (IC = 1.0 A, IB = 0.1 A)	VBE(sat)	-	1.1	V
Base–Emitter Turn–on Voltage (Note 1.) (I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 2.0 V)	VBE(on)	-	1.1	V
Cutoff Frequency (IC = 100 mA, $V_{CE}$ = 5.0 V, f = 100 MHz	fΤ	100	_	MHz
Output Capacitance (f = 1.0 MHz)	C <sub>obo</sub>	_	15	pF

Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%

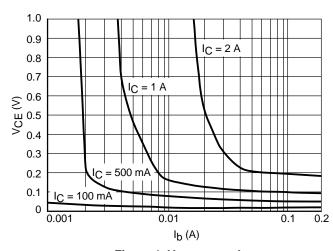


Figure 1. V<sub>CE</sub> versus I<sub>b</sub>

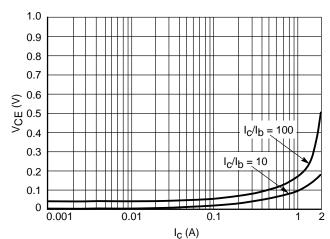


Figure 2. V<sub>CE</sub> versus I<sub>C</sub>

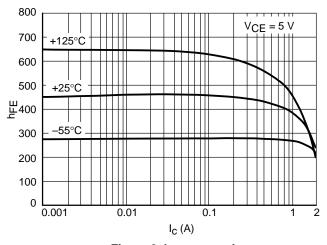


Figure 3. hFE versus I<sub>C</sub>

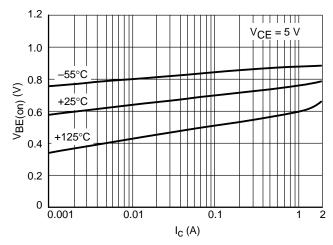


Figure 4. VBE(on) versus I<sub>C</sub>

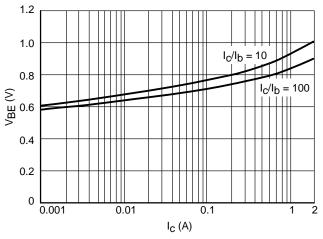


Figure 5. VBE(sat) versus Ic

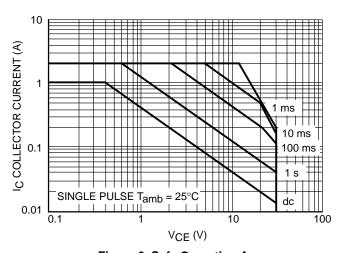


Figure 6. Safe Operating Area

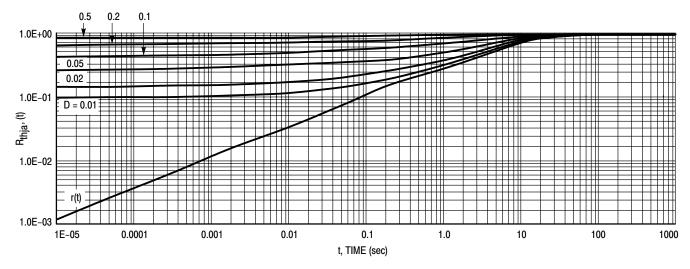
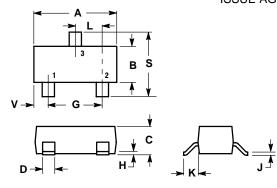


Figure 7. Normalized Thermal Response

# **PACKAGE DIMENSIONS**

SOT-23 (TO-236) CASE 318-08 **ISSUE AG** 



NOTES:

- DIMENSIONING AND TOI FRANCING PER ANSI DIMENSIO Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE
- 318-03 AND -07 OBSOLETE, NEW STANDARD

	INCHES		INCHES MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
٧	0.0177	0.0236	0.45	0.60

STYLE 6:

PIN 1. BASE

EMITTER

COLLECTOR

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